

MA125

Silicon epitaxial planer type

For switching circuits

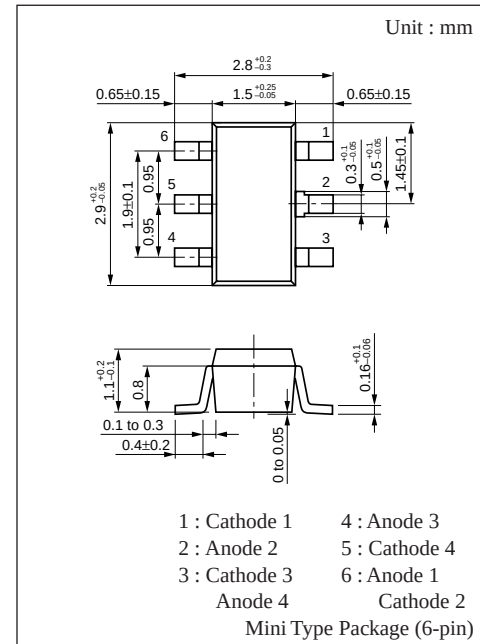
■ Features

- Four-element incorporated in one package, enabling high-density mounting

■ Absolute Maximum Ratings (Ta= 25°C)

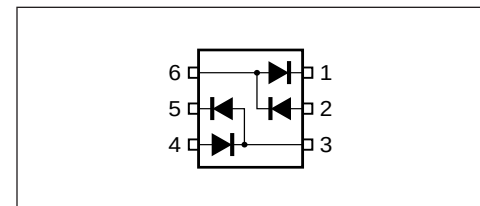
Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	40	V
Peak reverse voltage	V_{RM}	40	V
Forward current (DC)	I_F	*100	mA
Peak forward current	I_{FM}	*200	mA
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	- 55 to +150	°C

* Value in single diode used



Marking Symbol : M2I

■ Internal Connection



■ Electrical Characteristics (Ta= 25°C)

Parameter	Symbol	Condition	min	typ	max	Unit
Reverse current (DC)	I_R	$V_R = 40V$			100	nA
Forward voltage (DC)	V_F	$I_F = 100mA$			1.2	V
Reverse voltage (DC)	V_R	$I_R = 100\mu A$	40			V
Terminal capacitance	C_t	$V_R = 0V, f = 1MHz$			5	pF
Reverse recovery time	$t_{rr1}^{*1, 3}$	$I_F = 10mA, V_R = 6V$		150		ns
	$t_{rr2}^{*2, 3}$	$I_{rr} = 0.1 \cdot I_R, R_L = 100\Omega$		9		

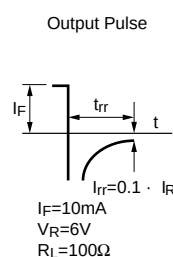
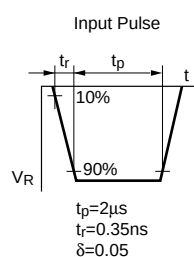
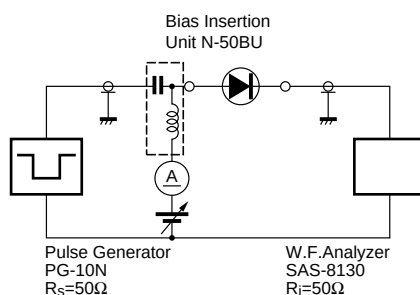
Note 1 : Rated input/output frequency : 100MHz

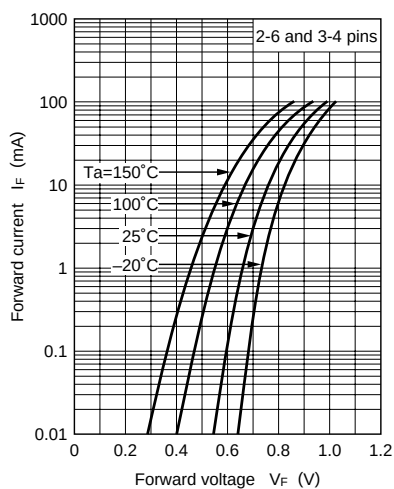
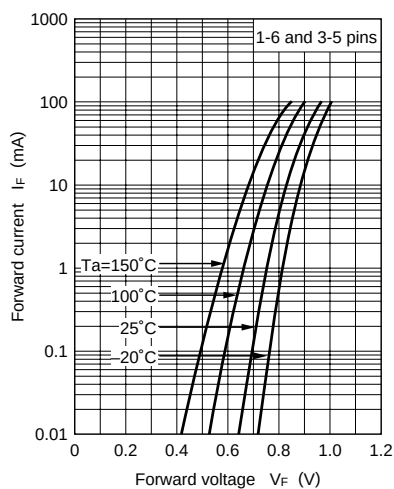
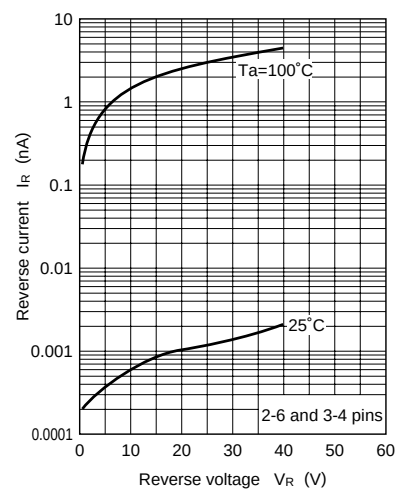
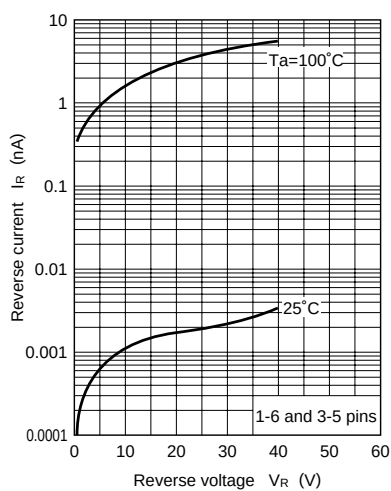
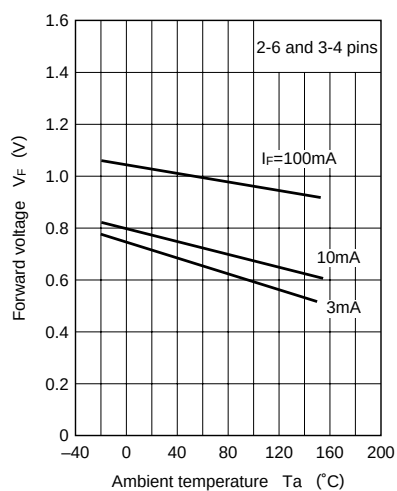
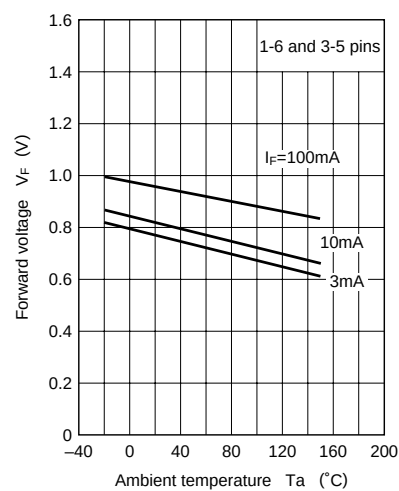
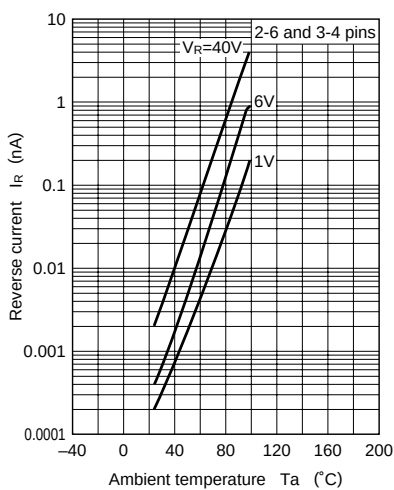
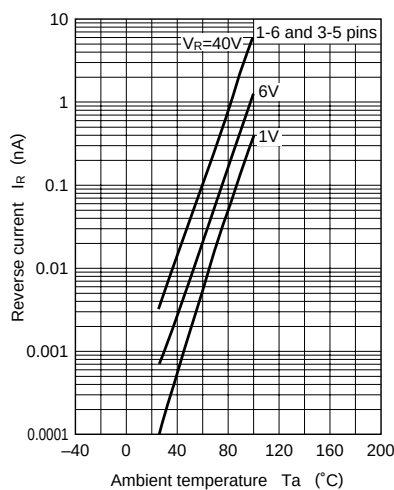
2 : *1 Between pins 1 and 6 Between pins 3 and 5

* 2 Between pins 2 and 6 Between pins 3 and 4

* t_{rr} measuring circuit

■ Marking



$I_F - V_F$  $I_F - V_F$  $I_R - V_R$  $I_R - V_R$  $V_F - T_a$  $V_F - T_a$  $I_R - T_a$  $I_R - T_a$  $C_t - V_R$ 